

**TITLE OF THE INVENTION: SUBSTRATE PROCESSING METHOD AND
SUBSTRATE PROCESSING APPARATUS**

ABSTRACT

A substrate processing method of supplying a process gas to a substrate, in which a first film and a second film that are silicon-containing films of different types are exposed on a surface, to selectively etch the first film that is a silicon oxide film, the method including: a protection process of supplying a fluid containing a silylating agent to the substrate in order to form, on a surface layer of the second film, a protective film that prevents etching of the second film; and an etching process of selectively etching the first film by supplying the process gas to the substrate having the protective film formed thereon.

[Fig. 2B]